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## Table of Contents

### Preface

Electronic Structure Analysis of Silicon Nanowires for High Conductivity in n- and p-channel Nanowire-FET <i>Y. Lee, T. Nagata, K. Kakushima, K. Shiraishi and H. Iwai</i>	1
Hole Mobility in Si(110) p-MOS Transistors <i>P. Gaubert, A. Teramoto and T. Ohmi</i>	7
Measurement of the Mechanical Stability of Semiconductor Line Structures in Relevant Media <i>D. Peter, M. Dalmer, H. Kruwinus, A. Lechner, L. Archer, E. Gaulhofer, A. Gigler, R. Stark and W. Bensch</i>	13
Analysis of Threshold Voltage Variations of FinFETs Relating to Short Channel Effects <i>Y. Kobayashi, A. Sachid, K. Tsutsui, K. Kakushima, P. Ahmet, V. Rao and H. Iwai</i>	23
Schottky Barrier Height Modulation by Er Insertion and Its Application to SB-MOSFETs <i>K. Noguchi, W. Hosoda, K. Matano, K. Kakushima, P. Ahmet, K. Tsutsui, N. Sugii, A. Chandorkar, T. Hattori and H. Iwai</i>	29
Micro and Nano R&D Fab Performance and Productivity A Lean Six-Sigma Approach <i>R. J. Olson, W. Hawkins, P. Piacente, R. Frank, J. Deluca, L. Douglas and G. Trant</i>	35
The Novel Highly-Selective Etching Process of SiO <sub>2</sub> to TiSix for Nano-Scale Device Fabrication <i>D. Hwang, K. Kim, Y. Lee and S. Chae</i>	47
Impurity Amplification in Ultra High Purity Hydrogen Bromide by Water Catalyzed Reactions from Different Cylinder Materials <i>A. Seymour, R. Torres, C. Wyse, J. Yao, T. Evdokimova, R. Pemberton, M. Raynor, J. Lee and W. Jung</i>	61

Multiple Defect Modes in Diamond Photonic Crystal <i>M. Thitsa, T. V. Nguyen and S. Albin</i>	71
Electrochemical Evaluation and Finite Element Structural Analysis of Si Wafer Surface Under Mechanical Stress <i>K. Sakata and T. Homma</i>	79
Investigation of THz Emission by p-GaAsSb <i>S. Hargreaves, L. Bignell, R. Lewis, D. Schoenherr, M. Saglam and H. Hartnagel</i>	87
Control of the Crystal Phase in Fe/Si Films by Using Thin Film Zone Melting Crystallization <i>T. Inoue, T. Shinsuke, Y. Tanaka and M. Ihara</i>	93
Temperature-Dependent PL Intensity in FLA-Synthesized and Hydrogen-Modified Silica Layers with Silicon Nanocrystals <i>V. Volodin, V. Stuchinsky, S. Cherkova, G. Kachurin and R. Yankov</i>	105
Author Index	113